

Vishay Siliconix

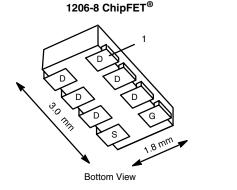
P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)		
- 20	0.062 at V _{GS} = - 4.5 V	- 5.1		
	0.068 at V _{GS} = - 3.6 V	- 4.9		
	0.085 at V _{GS} = - 2.5 V	- 4.4		
	0.120 at V _{GS} = - 1.8 V	- 3.7		

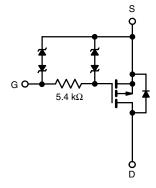
FEATURES

- Halogen-free According to IEC 61249-2-21
 Available
- ESD Protected^b 5000 V





Marking Code



P-Channel MOSFET

Ordering Information: Si5463EDC-T1-E3 (Lead (Pb)-free) Si5463EDC-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS	_A = 25 °C, unles	ss otherwise r	noted			
Parameter		Symbol	5 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	- 20		V	
Gate-Source Voltage		V _{GS}	± 12			
	T _A = 25 °C	– I _D	- 5.1	- 3.8		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 85 °C		- 3.7	- 2.7	٨	
Pulsed Drain Current		I _{DM}	- 15		A	
Continuous Source Current ^a		۱ _S	- 1.9	- 1.0		
	T _A = 25 °C	– P _D	2.3	1.25	W	
Maximum Power Dissipation ^a	T _A = 85 °C		1.2	0.65	vv	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	
Soldering Recommendations (Peak Temperature) ^{c, d}			260			

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
	t ≤ 5 s	R _{thJA}	45	55	
Maximum Junction-to-Ambient ^a	Steady State		84	100	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	20	25	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. When using HBM. The MM rating is 300 V.

c. See Reliability Manual for profile. The ChipFET is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

d. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

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SPECIFICATIONS $T_J = 25^{\circ}$	C, unless of	otherwise noted		-			
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \ \mu A$	- 0.45			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 4.5 V$			± 1.5		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 16 V, V _{GS} = 0 V			- 1	μA	
		V_{DS} = - 16 V, V_{GS} = 0 V, T_{J} = 85 °C	$_{\rm S}$ = - 16 V, V _{GS} = 0 V, T _J = 85 °C - 5				
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \leq$ - 5 V, V_{GS} = - 4.5 V	- 15			Α	
Drain-Source On-State Resistance ^a		V _{GS} = - 4.5 V, I _D = - 4.0 A		0.051	0.062		
	R _{DS(on)}	V _{GS} = - 3.6 V, I _D = - 3.5 A		0.056	0.068	Ω	
		V _{GS} = - 2.5 V, I _D = - 3.0 A		0.070	0.085		
		V _{GS} = - 1.8 V, I _D = - 1.5 A		0.100	0.120		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 5 V, I _D = - 4.0 A		10		S	
Diode Forward Voltage ^a	V _{SD}	I _S = - 1.0 A, V _{GS} = 0 V		- 0.75	- 1.2	V	
Dynamic ^b							
Total Gate Charge	Qg			9.7	15	nC	
Gate-Source Charge	Q _{gs}	V_{DS} = - 10 V, V_{GS} = - 4.5 V, I_{D} = - 4.0 A		2.7			
Gate-Drain Charge	Q _{gd}			1.4			
Turn-On Delay Time	t _{d(on)}			1.85	2.5	- μs	
Rise Time	t _r	V_{DD} = - 10 V, R_L = 10 Ω		3.2	4.5		
Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D}\cong$ - 1 A, V_GEN = - 4.5 V, R_G = 6 Ω		1.9	2.5		
Fall Time	t _f			3.2	4.5		

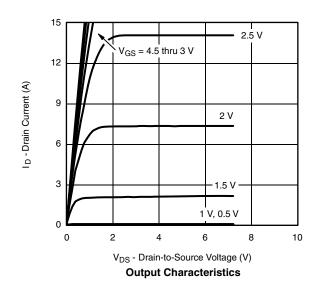
Notes:

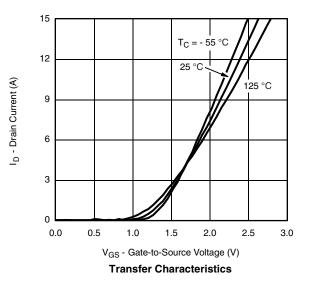
a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

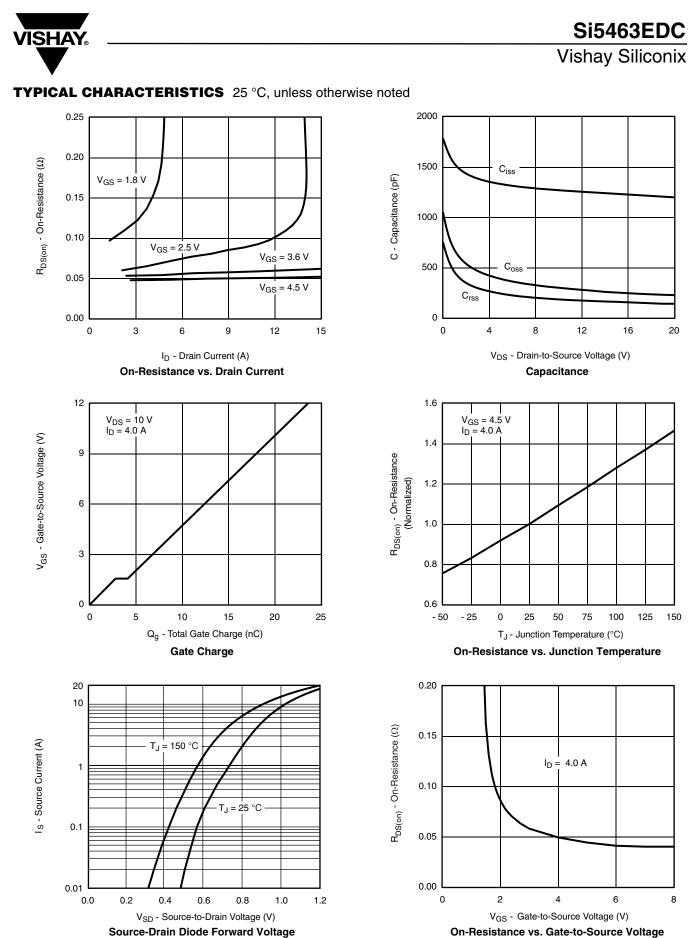
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



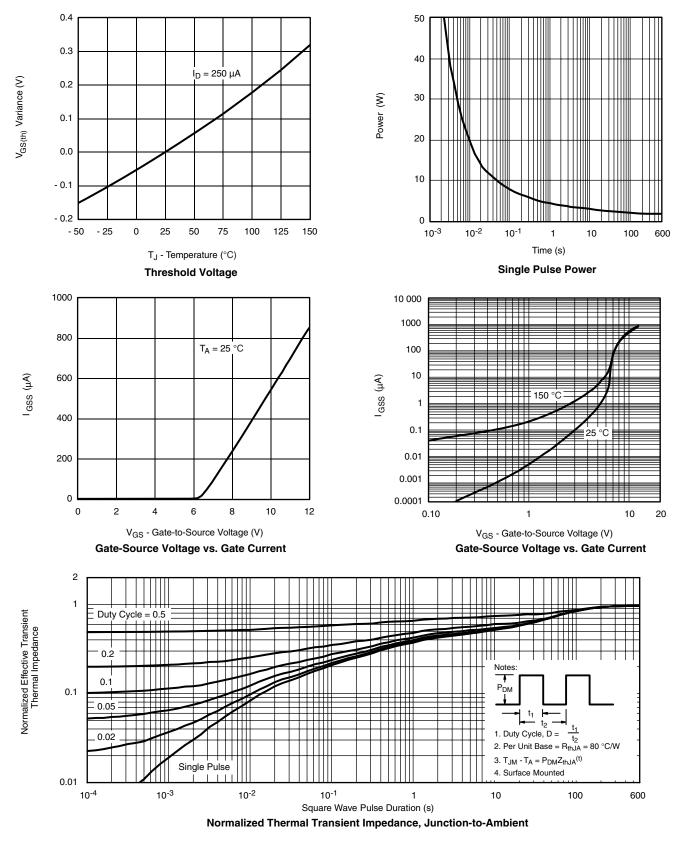




Si5463EDC

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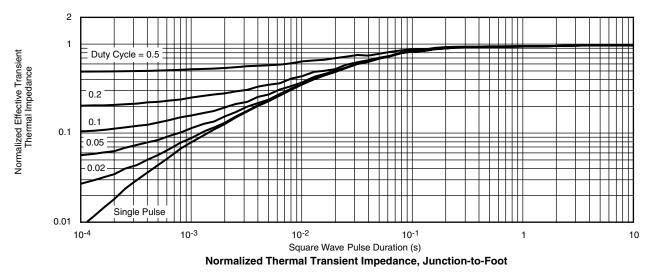




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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <u>www.vishay.com/ppg271364</u>.



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